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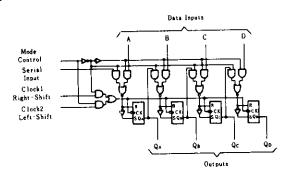
This 4-bit register features parallel and serial inputs, parallel outputs, mode control, and two clock inputs. The register has three mode operation:

- Parallel (broadside) load
- Shift right (the direction C_A toward Q_D)
- Shift left (the direction Q_D toward Q_A)

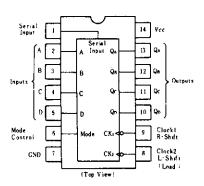
Parallel loading is accomplished by applying the four bits of data and taking the mode control input high. The data is loaded into the associated flip-flops and appears at the outputs after the high-to-low transition of the clock-2 input. During loading, the entry of serial data is inhibited. Shift right is accomplished on the high-to-low transition of clock-1 when the

mode control is low; shift left is accomplished on the high-tolow transition of clock-2 when the mode control is high by connecting the output of each flip-flop to the parallel input of the previous flip-flop (QD to input C, etc.) and serial data is entered at input D. The clock input may be applied commonly to clock-1 and clock-2 if both modes can be clocked from the same source. Changes at the mode control input should normally be made while both clock inputs are low: however, conditions described in the last three lines of the function table will also ensure that register contents are protected.

■BLOCK DIAGRAM



■PIN ARRANGEMENT



INFUNCTION TABLE

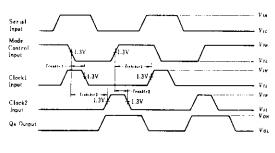
				Out	puts						
Mode	Clocks				Par	allel		Q _A	Q _B	\mathbf{Q}_{C}	Qυ
Control	2(L)	100	Serial	A	В	С	D	₩A	40	40	4 0
Н	Н	×	×	×	×	×	×	Qao	Qво	Q co	Qpo
Н	1	×	×	a	ь	c	d	a	b	c	d
Н	1	×	×	Q _B †	Qc†	Qn†	d.	QBn	Q _{Cn}	Q _{Dn}	d
L	L	Н	×	×	×	×	×	Qao	Qво	Qco	Quo
L	×	1	Н	×	×	×	×	Н	Q _{An}	Q _{Bn}	Qcn
L	×	ı	L	×	×	×	×	L	QAn	Q _{Bn}	Qca
1	L	L	×	×	×	×	×	Qao	Qво	Qco	Qυo
1	L	L	×	×	×	×	×	Qao	Qво	Qcσ	QDO
	L	H	×	×	×	×	×	QAO	Qво	Qco	Qno
<u>†</u>	Н	L.	×	×	×	×	×	QAO	Qво	Qco	Qpo
<u>†</u>	Н	Н	×	×	×	×	×	QAO	Qво	Qco	QDO

- Notes) 1. H; high level, L; low level, X; irrelevant
 - 2. †; transition from low to high level
 - 3. 4; transition from high to low level
 - 4. a~d; the level of steady-state input at inputs A,B,C, or D,
 - 5. QA0~QD0; the level of QA, QB, QC, or QD, respectively,
- before the indicated steady-state input conditions were established.
- 6. QAn~QDn; the level of QA, QB, QC, or QD, respectively, before the most-recent (†) transition of the clock.
- 7. †; Shifting left require external connection of QB to A, QC to B, and QD to C. Serial data is entered at input D.

HD74LS95B

TRECOMMENDED OPERATING CONDITIONS

Item	Symbol	min	typ	max	Unit	
Clock frequency	fclock	0	-	25	MHz	
Clock pulse width	ŧw(CK)	25	_	_	ns	
Setup time	tre	20		-	ית	
Hold time	th	10	_	_	ns	
Enable time 1	tenable 1	20	_		ns	
Enable time 2	tenable 2	20	-		ns	
Inhibit time 1	Linkibit 1	20	_	_	ns	
Inhibit time 2	Linkibit 2	20	_	_	ns	



Clock Enable/Inhibit Times

ELECTRICAL CHARACTERISTICS ($Ta = -20 \sim +75^{\circ}C$)

Item	Symbol	Test Condition	min	typ*	max	Unit	
To and analysis	VIH			2.0	_		v
Input voltage	VIL	-		-	_	0.8	V
	Voн	$V_{CC} = 4.75 \text{V}, V_{IH} = 2 \text{V}, V_{IL} = 0.8 \text{V}$	2.7		_	ν	
Output voltage	Fr	$V_{CC} = 4.75 \text{V}, V_{IH} = 2 \text{V},$	IoL = 4mA			0.4	ν
	Vol	$V_{IL}=0.8V$	IoL = 8mA	_		0.5	V
	Iтн	$V_{CC} = 5.25 \text{V}, V_I = 2.7 \text{V}$				20	μA
Input current	Iπ	$V_{CC} = 5.25 \text{V}, V_I = 0.4 \text{V}$		-	_	-0.4	mA
	It	$V_{CC} = 5.25 \text{ V}, V_i = 7 \text{ V}$				0.1	mА
Short-circuit output current Ios		$V_{CC}=5.25V$	•	-20		-100	mA
Supply current * * Icc		$V_{CC} = 5.25 \text{V}$	•		13	21	mА
Input clamp voltage VIK		$V_{CC} = 4.75$ V. $I_{IN} = -18$ m	4	- 1		-1.5	V

^{*} V_{CC}=5V, Ta=25°C

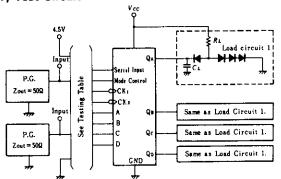
ESWITCHING CHARACTERISTICS ($V_{cc} = 5V$, $T_a = 25^{\circ}C$)

Item	Symbol	Test Conditions	min	typ	max	Unit
Maximum clock frequency	fmoz		25	36	•	MHz
	tplh	$C_L = 15 \text{pF}, R_L = 2 \text{k}\Omega$	-	18	27	ns
Propagation delay time	tPHL		_	21	32	ns

^{**}I_{CC} is measured with all outputs and serial input open; A,B,C, and D inputs grounded; mode control at 4.5V; and momentary 3V, then ground, applied both clock inputs.

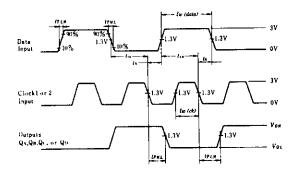
TESTING METHOD

1) Test Circuit



Notes) 1. C_L includes probe and jig capacitance. 2. All diodes are 1S2074 P.

Waveform

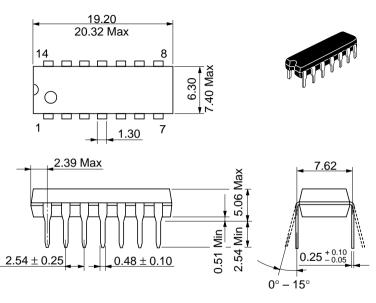


Note) 1. Input pulse: t_{TLH} , $t_{THL} \le 10$ ns, Data PRR = 500kHz Clock PRR=1MHz

2) Testing Table

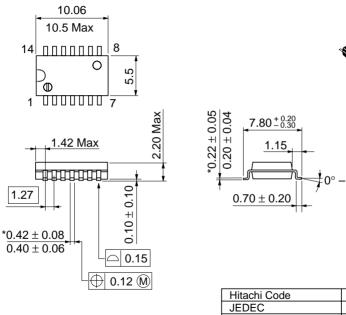
	From input	Inputs							Outputs				
ltem		CK-1	CK-2	Mode Control	Secial Inputs	A	В	С	D	Q۸	Qв	Qc	Qυ
	CK-1→Q	IN	4.5V	0V	IN	4.5V	4.5V	1.5V	4.5V	OUT	OUT	OUT	OUT
fmax	CK-2→Q	4.5V	IN	4.5V	4.5V	IN	IN	IN	IN	OUT	OUT	OUT	OUT
tPLH	CK-1→Q	IN	1.5V	0V	IN	4.5V	4.5V	4.5V	4.5V	OUT	OUT	OUT	OUT
tPHL	CK-2→Q	4.5V	IN	4.5V	4.5V	IN	IN	IN	IN	OUT	OUT	OUT	OUT

Unit: mm



Hitachi Code	DP-14
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.97 g

Unit: mm



*Dimension including the plating thickness
Base material dimension

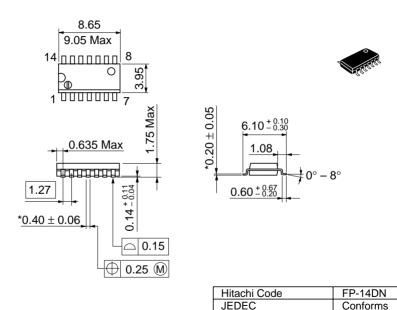
Hitachi Code FP-14DA

JEDEC —

EIAJ Conforms

Weight (reference value) 0.23 g

Unit: mm



EIAJ

Weight (reference value)

Conforms

0.13 g

*Pd plating

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